

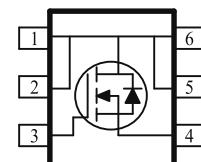
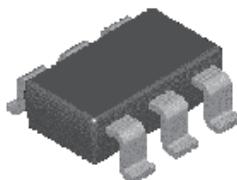
## N-Channel 20V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low  $r_{DS(on)}$  provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

### PRODUCT SUMMARY

<b>V<sub>DS</sub> (V)</b>	<b>r<sub>DS(on)</sub> (OHM)</b>	<b>I<sub>D</sub> (A)</b>
20	0.032 @ V <sub>GS</sub> = 4.5 V	6.0
	0.044 @ V <sub>GS</sub> = 2.5V	5.0



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	
Continuous Drain Current <sup>a</sup>	I <sub>D</sub>	6.0	A
		4.6	
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	±20	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	1.6	A
Power Dissipation <sup>a</sup>	P <sub>D</sub>	2.0	W
		1.3	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>THJA</sub>	62.5	°C/W
		110	

#### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

## SPECIFICATIONS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
<b>Static</b>						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	0.7			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 8 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 16 \text{ V}$ , $V_{GS} = 0 \text{ V}$		1		uA
		$V_{DS} = 16 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 55^\circ\text{C}$		10		
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}$ , $V_{GS} = 4.5 \text{ V}$	10			A
Drain-Source On-Resistance <sup>A</sup>	$r_{DS(on)}$	$V_{GS} = 4.5 \text{ V}$ , $I_D = 6.0 \text{ A}$		32		mOHM
		$V_{GS} = 2.5 \text{ V}$ , $I_D = 5.0 \text{ A}$		44		
Forward Tranconductance <sup>A</sup>	$g_{fs}$	$V_{DS} = 10 \text{ V}$ , $I_D = 4.0 \text{ A}$		11.3		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1.6 \text{ A}$ , $V_{GS} = 0 \text{ V}$		0.75		V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 4.5 \text{ V}$ , $I_D = 4.0 \text{ A}$		5.0		nC
Gate-Source Charge	$Q_{gs}$			1.2		
Gate-Drain Charge	$Q_{gd}$			2.0		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10 \text{ V}$ , $R_L = 15 \text{ O}$ , $I_D = 1 \text{ A}$ , $V_{GEN} = 4.5 \text{ V}$		8		ns
Rise Time	$t_r$			24		
Turn-Off Delay Time	$t_{d(off)}$			35		
Fall-Time	$t_f$			10		

### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

## Typical Electrical Characteristics (N-Channel)

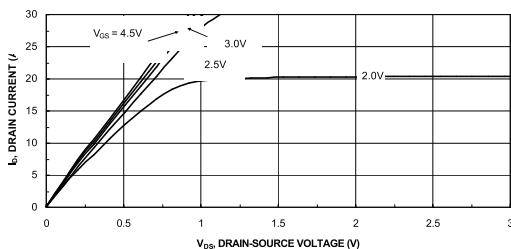


Figure 1. Output Characteristics

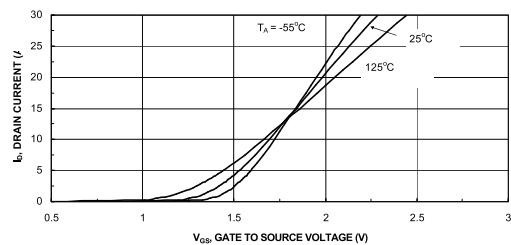


Figure 2. Transfer Characteristics

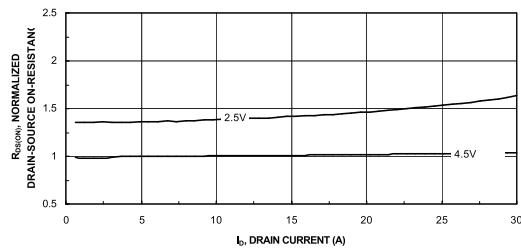


Figure 3. On-Resistance vs. Drain Current

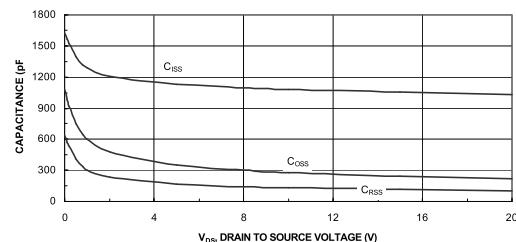


Figure 4. Capacitance

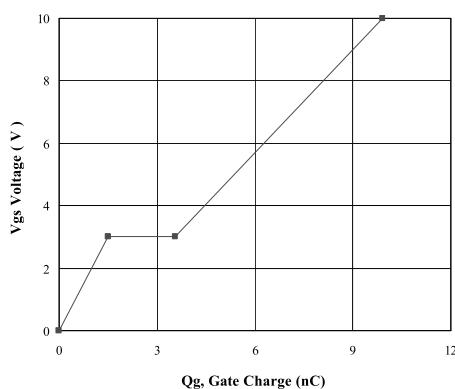


Figure 5. Gate Charge

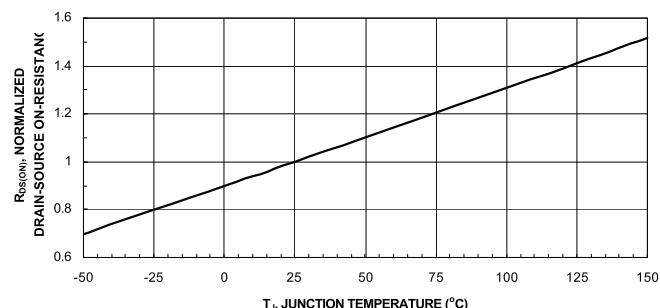


Figure 6. On-Resistance vs. Junction Temperature

## Typical Electrical Characteristics (N-Channel)

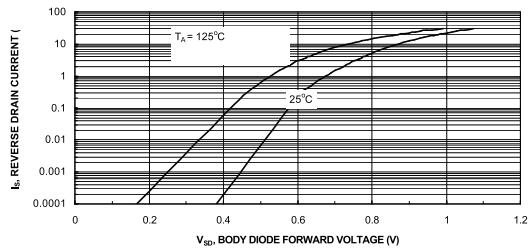


Figure 7. Source-Drain Diode Forward Voltage

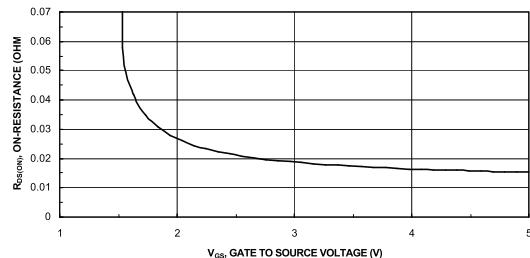


Figure 8. On-Resistance vs. Gate-to-Source Voltage

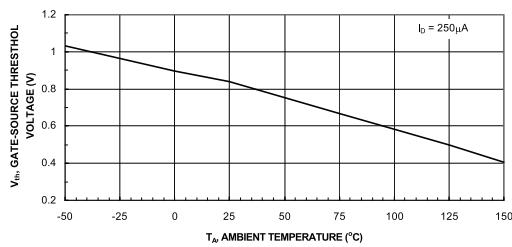


Figure 9. Threshold Voltage

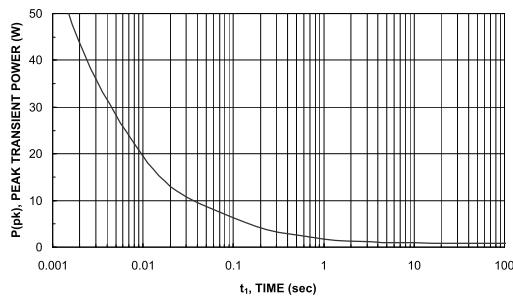


Figure 10. Single Pulse Power

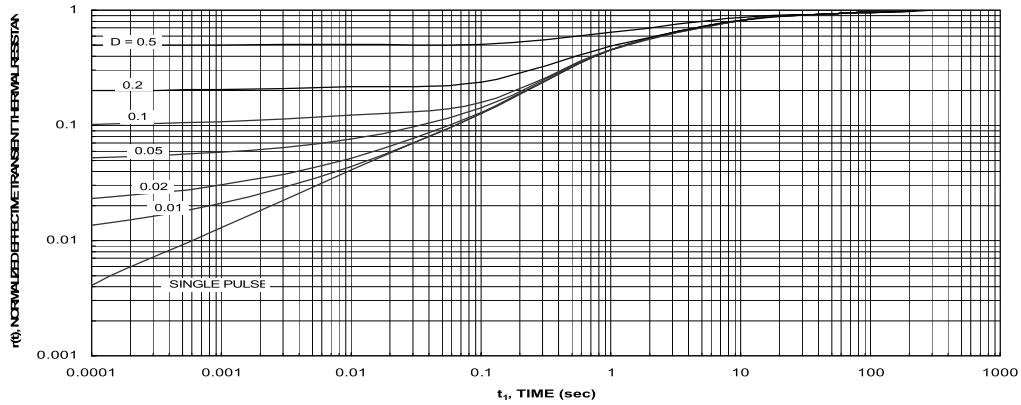
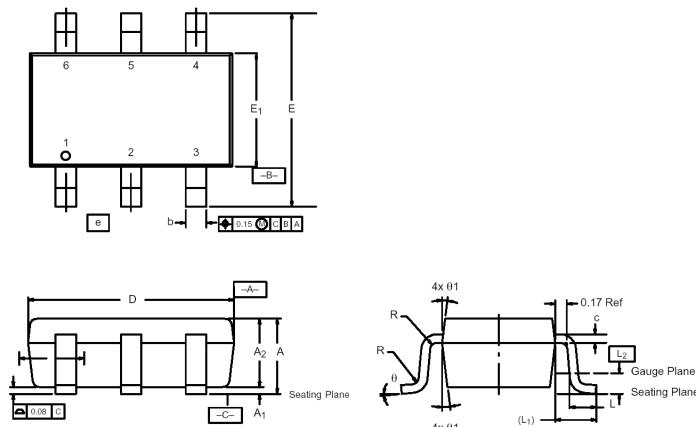


Figure 11. Normalized Thermal Transient Impedance, Junction-to-Ambient

## Package Information

### TSOP-6: 6LEAD



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
<b>A</b>	0.91	—	1.10	0.036	—	0.043
<b>A<sub>1</sub></b>	0.01	—	0.10	0.0004	—	0.004
<b>A<sub>2</sub></b>	0.84	—	1.00	0.033	0.038	0.039
<b>b</b>	0.30	0.32	0.45	0.012	0.013	0.018
<b>c</b>	0.10	0.15	0.20	0.004	0.006	0.008
<b>D</b>	2.95	3.05	3.10	0.116	0.120	0.122
<b>E</b>	2.70	2.85	2.98	0.106	0.112	0.117
<b>E<sub>1</sub></b>	1.55	1.65	1.70	0.061	0.065	0.067
<b>e</b>	1.00 BSC			0.0394 BSC		
<b>L</b>	0.35	—	0.50	0.014	—	0.020
<b>L<sub>1</sub></b>	0.60 Ref			0.024 Ref		
<b>L<sub>2</sub></b>	0.25 BSC			0.010 BSC		
<b>R</b>	0.10	—	—	0.004	—	—
<b>θ</b>	0°	4°	8°	0°	4°	8°
<b>θ<sub>1</sub></b>	7° Nom			7° Nom		

# Ordering information

- AM3446N-T1-XX
  - A: Analog Power
  - M: MOSFET
  - 3446: Part number
  - N: N-Channel
  - T1: Tape & reel
  - XX: Blank: Standard  
PF: Leadfree